

3 Amp. Surface Mounted Schottky Barrier Rectifier

<p>Dimensions in mm.</p> <p>Top view dimensions: 7.8 ± 0.3, 1.25 ± 0.25, 1.05 ± 0.2, 2.2 ± 0.3, 0.2, 1.25 ± 0.25, 5.9 ± 0.3, 3 ± 0.2, 0.15 ± 0.1.</p> <p>Side view dimensions: 0.15 ± 0.1.</p> <p>Soldering pad dimensions: 3.8, 2.8, 7.2.</p> <p>Marking: UAB, H, Week code, Year code, Type No. Cross.</p>	<p>CASE: SMC/DO-214AB (Plastic)</p>	<p>Voltage 20 V to 60 V</p>	<p>Current 3.0 A</p>
<ul style="list-style-type: none"> • Metal Silicon Junction, majority carrier conduction • High current capability, low forward voltage drop • Guardring for overvoltage protection • Low power loss, high efficiency • High surge capability • Plastic material carries U/L recognition 94VO • Low profile package • Easy pick and place 			

Maximum Ratings, according to IEC publication No. 134

		FSS32	FSS33	FSS34	FSS35	FSS36
Marking Code		C1	C2	C3	C4	C5
V_{RRM}	Peak recurrent reverse voltage (V)	20	30	40	50	60
V_{RMS}	Maximum RMS voltage (V)	14	21	28	35	42
V_{DC}	Maximum DC blocking voltage (V)	20	30	40	50	60
$I_{F(AV)}$	Maximum average Forward current.	3 A				
I_{FSM}	8.3 ms. peak forward surge current (Jedec Method)	100 A				
T_j	Operating temperature range	- 65 to + 125 °C			- 65 to + 150 °C	
T_{stg}	Storage temperature range	- 65 to + 150 °C				

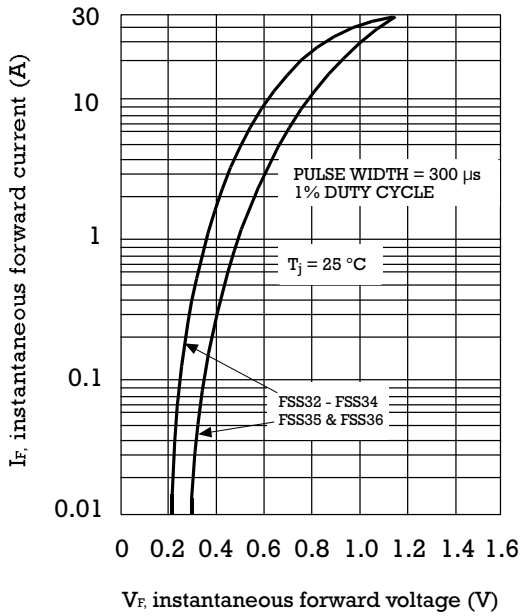
Electrical Characteristics at $T_{amb} = 25\text{ °C}$

V_F	Max. forward voltage drop at $I_F = 3.0\text{ A}$ ⁽¹⁾	0.55 V	0.75 V
I_R	Max. Instantaneous reverse current at V_{RRM} ⁽¹⁾	$T_a = 25\text{ °C}$	0.5 mA
		$T_a = 100\text{ °C}$	20 mA
R_{thj-a} R_{thj-l}	Typical Thermal Resistance	55 °C/W 17 °C/W	

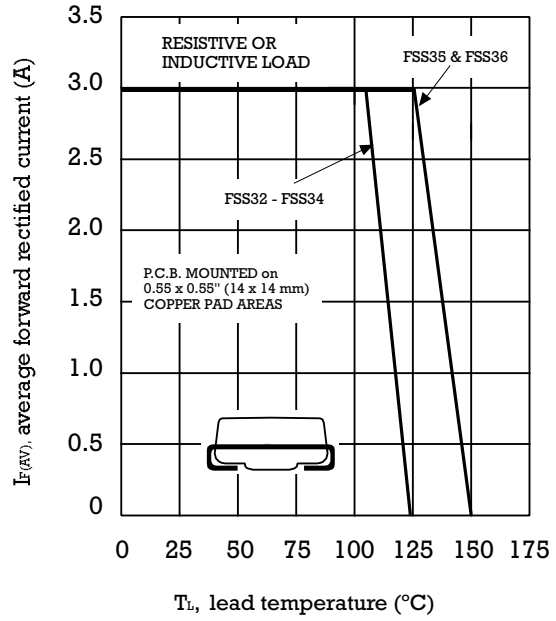
NOTE: Thermal Resistance from junction to lead or to ambient PCB mounted with 14x14 mm copper pads areas.

(1) Pulse test: 300µs pulse width, 1% duty cycle.

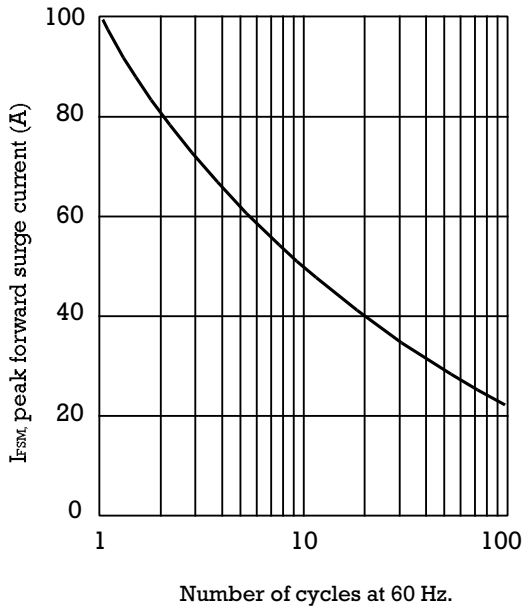
TYPICAL FORWARD CHARACTERISTIC



FORWARD CURRENT DERATING CURVE



MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



TYPICAL JUNCTION CAPACITANCE

